2.5V Drive Nch MOS FET RTQ035N03

Structure

Silicon N-channel MOS FET

● Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).
- 3) Low voltage drive (2.5V drive).

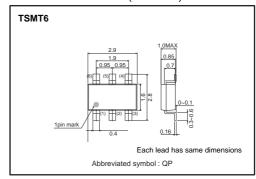
Applications

Switching

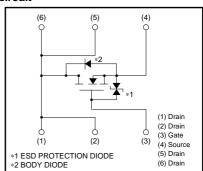
Packaging specifications

	Package	Taping	
Type	Code	TR	
	Basic ordering unit (pieces)	3000	
RTQ035N03		0	

●External dimensions (Unit : mm)



•Inner circuit



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	30	V	
Gate-source voltage		V _{GSS}	12	V	
Drain current	Continuous	I_D	±3.5	Α	
	Pulsed	I _{DP} *1	±15	Α	
Source current	Continuous	Is	1.0	Α	
(Body diode)	Pulsed	I _{SP} *1	4.0	Α	
Total power dissipation		P _D *2	1.25	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

^{*1} Pw≤10μs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	100	°C/W

^{*} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	10	μΑ	Vgs=12V, Vps=0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	_	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.5	_	1.5	V	V _{DS} = 10V, I _D = 1mA
		_	38	54	mΩ	I _D = 3.5A, V _{GS} = 4.5V
Static drain-source on-state resistance	R _{DS (on)} *	-	40	56	mΩ	I _D = 3.5A, V _{GS} = 4.0V
resistance		-	55	77	mΩ	I _D = 3.5A, V _{GS} = 2.5V
Forward transfer admittance	Y _{fs} *	3.0	_	_	S	V _{DS} = 10V, I _D = 3.5A
Input capacitance	Ciss	-	285	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	90	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	55	_	pF	f=1MHz
Turn-on delay time	t _{d (on)} *	-	8	_	ns	V _{DD} ≒ 15V
Rise time	tr *	-	12	_	ns	ID= 1.75A
Turn-off delay time	t _{d (off)} *	_	29	_	ns	V _{GS} = 4.5V R _L =8.57Ω
Fall time	t _f *	-	13	_	ns	R _G =10Ω
Total gate charge	Qg *	_	4.6	6.4	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	_	0.7	-	nC	V _{GS} = 4.5V
Gate-drain charge	Q _{gd} *	_	1.5	_	nC	I _D = 3.5A

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	-	_	1.2	V	I _S = 4A, V _{GS} =0V

*Pulsed

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